# Low-power Schmitt trigger inverter Rev. 6 — 28 June 2012

**Product data sheet** 

#### **General description** 1.

The 74AUP1G14 provides a single inverting Schmitt trigger which accepts standard input signals. It is capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

This device ensures a very low static and dynamic power consumption across the entire V<sub>CC</sub> range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I<sub>OFF</sub>.

The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage  $V_{T+}$  and the negative voltage  $V_{T-}$  is defined as the input hysteresis voltage V<sub>H</sub>.

#### **Features and benefits** 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

# **Applications**

- Wave and pulse shaper
- Astable multivibrator
- Monostable multivibrator



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# 4. Ordering information

Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74AUP1G14GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1						
74AUP1G14GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886						
74AUP1G14GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891						
74AUP1G14GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115						
74AUP1G14GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202						
74AUP1G14GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226						

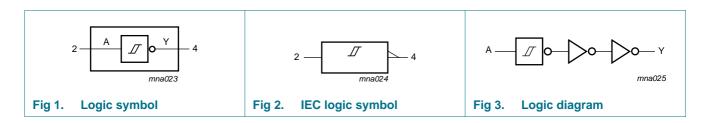
# 5. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74AUP1G14GW	pF
74AUP1G14GM	pF
74AUP1G14GF	pF
74AUP1G14GN	pF
74AUP1G14GS	pF
74AUP1G14GX	pF

<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

# 6. Functional diagram



# 7. Pinning information

### 7.1 Pinning





### 7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
n.c.	1	1	not connected
A	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
$V_{CC}$	5	6	supply voltage

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# 8. Functional description

Table 4. Function table[1]

Input	Output
Α	Υ
L	Н
Н	L

<sup>[1]</sup> H = HIGH voltage level;

L = LOW voltage level.

# 9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
l <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] _	250	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		8.0	3.6	V
$V_{I}$	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; V <sub>CC</sub> = 0 V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C

<sup>[2]</sup> For TSSOP5 packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K.
For XSON6 and X2SON5 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

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# 11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = -20 \mu A$ ; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l <sub>l</sub>	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
l <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0 = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.2	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.5	μΑ
Δl <sub>CC</sub>	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	$V_I = GND \text{ or } V_{CC}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	1.1	-	pF
Co	output capacitance	$V_O = GND$ ; $V_{CC} = 0 V$	-	1.7	-	pF
T <sub>amb</sub> = -	40 °C to +85 °C					
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = -20 \mu\text{A};  V_{CC} = 0.8  \text{V}  \text{to}  3.6  \text{V}$	V <sub>CC</sub> - 0.1	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7 \text{ mA}$ ; $V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}$ ; $V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_O = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
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 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{OL}$	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_{O}$ = 1.9 mA; $V_{CC}$ = 1.65 V	-	-	0.35	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l <sub>l</sub>	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_I$ or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
$\Delta I_{OFF}$	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μΑ
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.9	μΑ
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
T <sub>amb</sub> = -	40 °C to +125 °C					
V <sub>OH</sub>	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_{O} = -20 \mu\text{A};  V_{CC} = 0.8 \text{V} \text{to} 3.6 \text{V}$	V <sub>CC</sub> – 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = 20 \mu A$ ; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	٧
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	٧
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}$ ; $V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}$ ; $V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.50	V
l <sub>l</sub>	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V			±0.75	μΑ

Table 7. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$ to 0.2 V	-	-	±0.75	μΑ
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	1.4	μΑ
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

# 12. Dynamic characteristics

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C		–40 °C to +125 °C			Unit		
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 pl	F									
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	19.9	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.7	5.9	11.0	2.4	11.1	11.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.6	4.3	6.6	2.4	7.1	7.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.1	3.7	5.4	2.0	6.0	6.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	3.0	4.1	1.7	4.5	4.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.9	2.8	3.6	1.5	3.9	4.0	ns
C <sub>L</sub> = 10	oF									
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	23.4	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.9	6.8	12.7	2.8	12.8	12.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.8	5.0	7.7	2.6	8.2	8.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.7	4.2	6.2	2.5	6.7	7.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.3	3.6	4.8	2.1	5.2	5.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	3.3	4.3	2.0	4.5	4.7	ns
C <sub>L</sub> = 15	oF									
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	26.9	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	7.6	14.3	3.0	14.5	14.7	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.3	5.5	8.6	2.9	9.4	9.8	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.8	4.7	7.0	2.8	7.7	8.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.7	4.0	5.5	2.4	5.9	6.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.6	3.8	4.8	2.2	5.2	5.4	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-4	0 °C to +1	25 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]			'			•	'
		$V_{CC} = 0.8 \text{ V}$		-	37.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.0	9.8	18.7	3.9	19.6	20.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.7	7.1	11.2	3.8	12.3	12.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		3.6	6.0	9.1	3.6	10.0	10.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		3.5	5.2	6.9	3.2	7.5	7.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		3.3	4.8	6.1	3.1	7.1	7.4	ns
$C_L = 5 p$	F, 10 pF, 15 pF and	30 pF								
$C_{PD}$		$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]							
	capacitance	$V_{CC} = 0.8 \text{ V}$		-	2.6	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	2.9	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	3.1	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.7	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	4.3	-	-	-	-	pF

- [1] All typical values are measured at nominal  $V_{CC}$ .
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

fo = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

#### 13. Waveforms

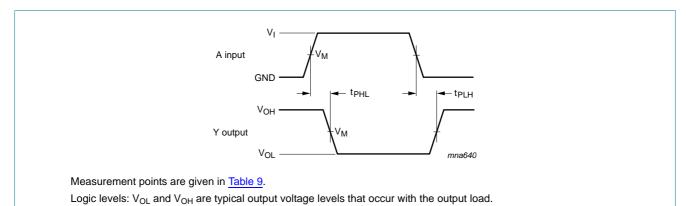


Fig 8. The data input (A) to output (Y) propagation delays

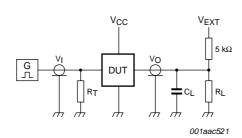
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#### Low-power Schmitt trigger inverter

Table 9. Measurement points

Supply voltage	Output	Input						
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>I</sub>	$t_r = t_f$				
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V <sub>CC</sub>	≤ 3.0 ns				



Test data is given in Table 10.

Definitions for test circuit:

R<sub>L</sub> = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

V<sub>EXT</sub> = External voltage for measuring switching times.

Fig 9. Load circuitry for switching times

Table 10. Test data

Supply voltage	Load	V <sub>EXT</sub>				
V <sub>CC</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$	

<sup>[1]</sup> For measuring enable and disable times  $R_L$  = 5 k $\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

#### 14. Transfer characteristics

Table 11. Transfer characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 25 °	C					
V <sub>T+</sub>	positive-going	see Figure 10 and Figure 11				
	threshold voltage	$V_{CC} = 0.8 \text{ V}$	0.30	-	0.60	V
		V <sub>CC</sub> = 1.1 V	0.53	-	0.90	V
		$V_{CC} = 1.4 \text{ V}$	0.74	-	1.11	V
		V <sub>CC</sub> = 1.65 V	0.91	-	1.29	V
		$V_{CC} = 2.3 \text{ V}$	1.37	-	1.77	V
		V <sub>CC</sub> = 3.0 V	1.88	-	2.29	V

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 Table 11.
 Transfer characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 9</u>.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{T-}$	negative-going	see Figure 10 and Figure 11				
	threshold voltage	V <sub>CC</sub> = 0.8 V	0.10	-	0.60	V
		V <sub>CC</sub> = 1.1 V	0.26	-	0.65	V
		V <sub>CC</sub> = 1.4 V	0.39	-	0.75	V
		V <sub>CC</sub> = 1.65 V	0.47	-	0.84	V
		V <sub>CC</sub> = 2.3 V	0.69	-	1.04	V
		V <sub>CC</sub> = 3.0 V	0.88	-	1.24	V
V <sub>H</sub>	hysteresis voltage	see <u>Figure 10</u> , <u>Figure 11</u> , <u>Figure 12</u> and <u>Figure 13</u>				
		V <sub>CC</sub> = 0.8 V	0.07	-	0.50	V
		V <sub>CC</sub> = 1.1 V	0.08	-	0.46	V
		V <sub>CC</sub> = 1.4 V	0.18	-	0.56	V
		V <sub>CC</sub> = 1.65 V	0.27	-	0.66	V
		V <sub>CC</sub> = 2.3 V	0.53	-	0.92	V
		V <sub>CC</sub> = 3.0 V	0.79	-	1.31	V
T <sub>amb</sub> = -40	°C to +85 °C					
V <sub>T+</sub>	positive-going threshold voltage	see Figure 10 and Figure 11				
		V <sub>CC</sub> = 0.8 V	0.30	-	0.60	V
		V <sub>CC</sub> = 1.1 V	0.53	-	0.90	V
		V <sub>CC</sub> = 1.4 V	0.74	-	1.11	V
		V <sub>CC</sub> = 1.65 V	0.91	-	1.29	V
		V <sub>CC</sub> = 2.3 V	1.37	-	1.77	V
		V <sub>CC</sub> = 3.0 V	1.88	-	2.29	V
$V_{T-}$	negative-going	see Figure 10 and Figure 11				
	threshold voltage	V <sub>CC</sub> = 0.8 V	0.10	-	0.60	V
		V <sub>CC</sub> = 1.1 V	0.26	-	0.65	V
		V <sub>CC</sub> = 1.4 V	0.39	-	0.75	V
		V <sub>CC</sub> = 1.65 V	0.47	-	0.84	V
		V <sub>CC</sub> = 2.3 V	0.69	-	1.04	V
		V <sub>CC</sub> = 3.0 V	0.88	-	1.24	V
V <sub>H</sub>	hysteresis voltage	see <u>Figure 10</u> , <u>Figure 11</u> , <u>Figure 12</u> and <u>Figure 13</u>				
		V <sub>CC</sub> = 0.8 V	0.07	-	0.50	V
		V <sub>CC</sub> = 1.1 V	0.08	-	0.46	V
		V <sub>CC</sub> = 1.4 V	0.18	-	0.56	V
		V <sub>CC</sub> = 1.65 V	0.27	-	0.66	V
		V <sub>CC</sub> = 2.3 V	0.53	-	0.92	V
		V <sub>CC</sub> = 3.0 V	0.79	-	1.31	V

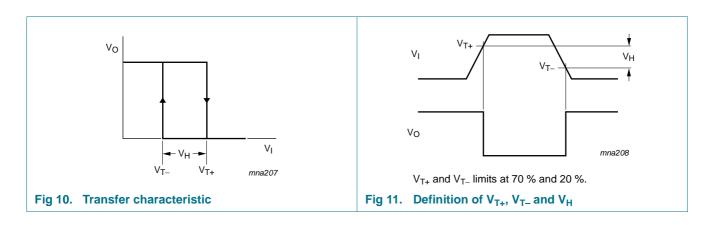
Low-power Schmitt trigger inverter

 Table 11.
 Transfer characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = -40	°C to +125 °C					
$V_{T+}$	positive-going	see Figure 10 and Figure 11				
	threshold voltage	V <sub>CC</sub> = 0.8 V	0.30	-	0.62	V
		V <sub>CC</sub> = 1.1 V	0.53	-	0.92	V
		V <sub>CC</sub> = 1.4 V	0.74	-	1.13	V
		V <sub>CC</sub> = 1.65 V	0.91	-	1.31	V
		V <sub>CC</sub> = 2.3 V	1.37	-	1.80	V
		V <sub>CC</sub> = 3.0 V	1.88	-	2.32	V
$V_{T-}$	negative-going threshold voltage	see Figure 10 and Figure 11				
		V <sub>CC</sub> = 0.8 V	0.10	-	0.60	V
		V <sub>CC</sub> = 1.1 V	0.26	-	0.65	V
		V <sub>CC</sub> = 1.4 V	0.39	-	0.75	V
		V <sub>CC</sub> = 1.65 V	0.47	-	0.84	V
		V <sub>CC</sub> = 2.3 V	0.69	-	1.04	V
		V <sub>CC</sub> = 3.0 V	0.88	-	1.24	V
V <sub>H</sub>	hysteresis voltage	see <u>Figure 10</u> , <u>Figure 11</u> , <u>Figure 12</u> and <u>Figure 13</u>				
		V <sub>CC</sub> = 0.8 V	0.07	-	0.50	V
		V <sub>CC</sub> = 1.1 V	0.08	-	0.46	V
		V <sub>CC</sub> = 1.4 V	0.18	-	0.56	V
		V <sub>CC</sub> = 1.65 V	0.27	-	0.66	V
		V <sub>CC</sub> = 2.3 V	0.53	-	0.92	V
		V <sub>CC</sub> = 3.0 V	0.79	-	1.31	V

# 15. Waveforms transfer characteristics



Low-power Schmitt trigger inverter

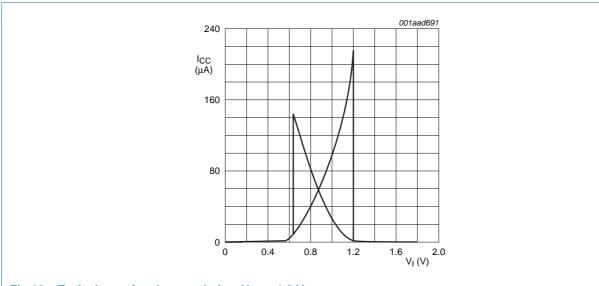


Fig 12. Typical transfer characteristics;  $V_{CC} = 1.8 \text{ V}$ 

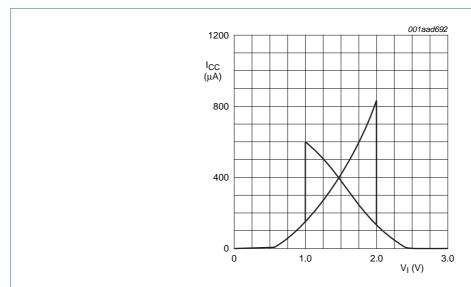


Fig 13. Typical transfer characteristics;  $V_{CC} = 3.0 \text{ V}$ 

Low-power Schmitt trigger inverter

# 16. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $P_{ad} = f_i \times (t_r \times I_{CC(AV)} + t_f \times I_{CC(AV)}) \times V_{CC}$  where:

 $P_{ad}$  = additional power dissipation ( $\mu W$ );

 $f_i = input frequency (MHz);$ 

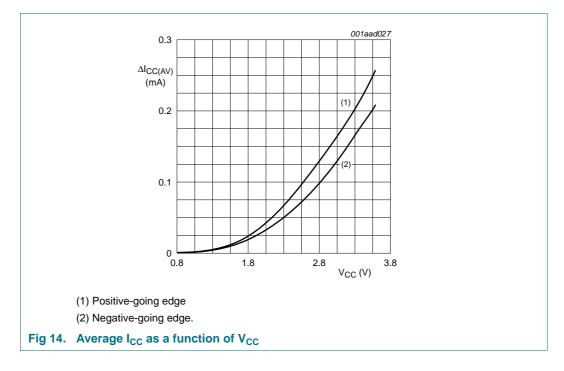
 $t_r$  = input rise time (ns); 10 % to 90 %;

 $t_f$  = input fall time (ns); 90 % to 10 %;

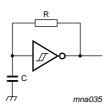
 $I_{CC(AV)}$  = average additional supply current ( $\mu A$ ).

Average I<sub>CC</sub> differs with positive or negative input transitions, as shown in Figure 14.

An example of a relaxation circuit using the 74AUP1G14 is shown in Figure 15.



#### Low-power Schmitt trigger inverter



$$f = \frac{1}{T} \approx \frac{1}{a \times RC}$$

Average values for variable a are given in <u>Table 12</u>.

Fig 15. Relaxation oscillator

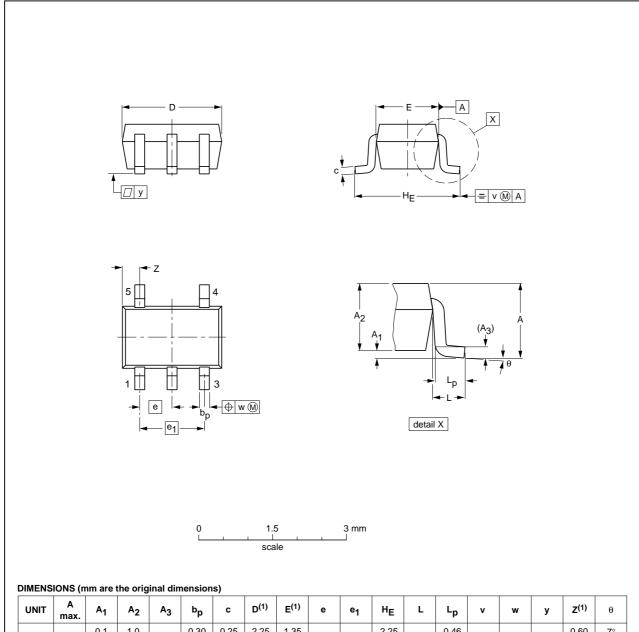
#### Table 12. Variable values

Supply voltage	Variable a
1.1 V	1.28
1.5 V	1.22
1.8 V	1.24
2.8 V	1.34
3.3 V	1.45

# 17. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UN	T A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	HE	L	L <sub>p</sub>	v	w	у	Z <sup>(1)</sup>	θ
mr	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

	OUTLINE		REFER	EUROPEAN	ISSUE DATE			
,	VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
	SOT353-1		MO-203	SC-88A			<del>-00-09-01-</del> 03-02-19	

Fig 16. Package outline SOT353-1 (TSSOP5)

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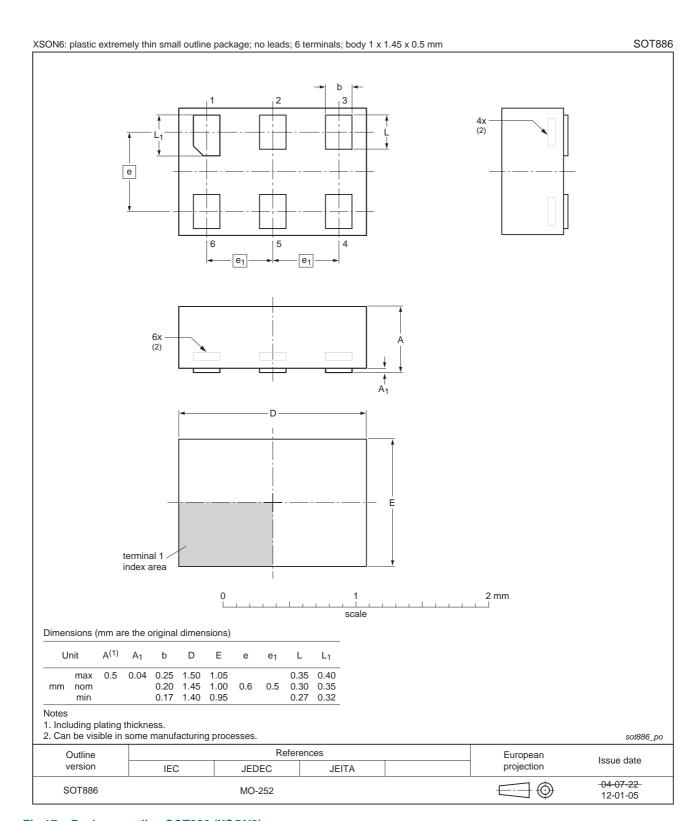


Fig 17. Package outline SOT886 (XSON6)

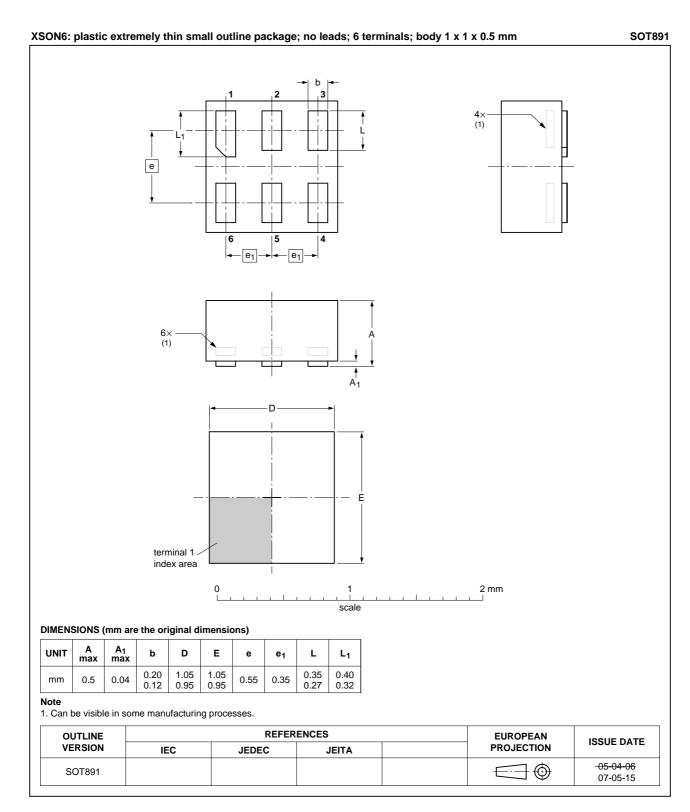


Fig 18. Package outline SOT891 (XSON6)

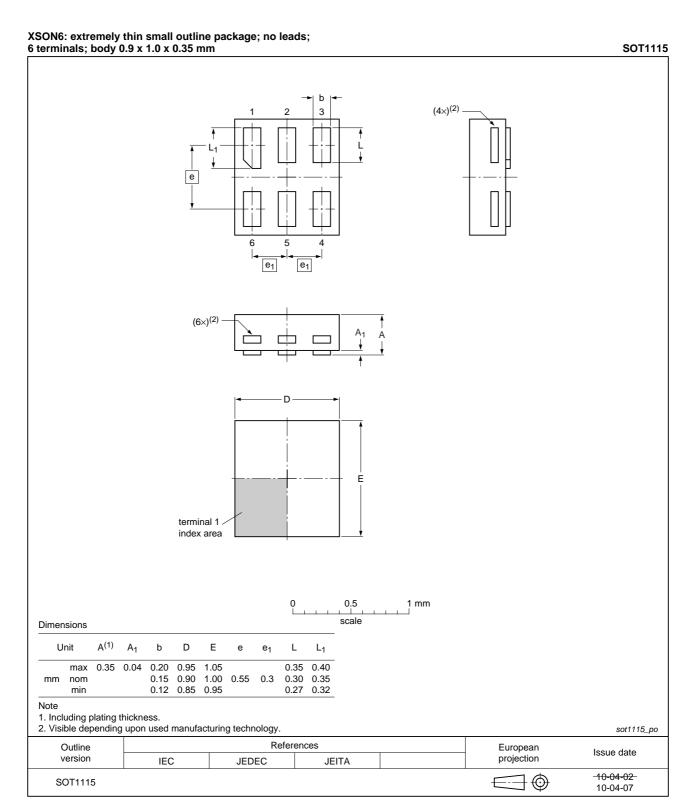


Fig 19. Package outline SOT1115 (XSON6)

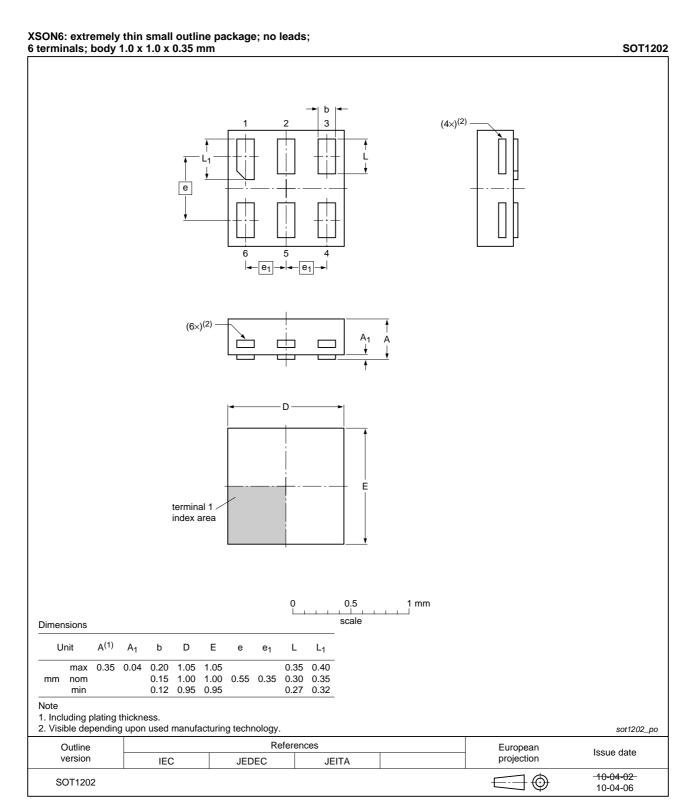


Fig 20. Package outline SOT1202 (XSON6)

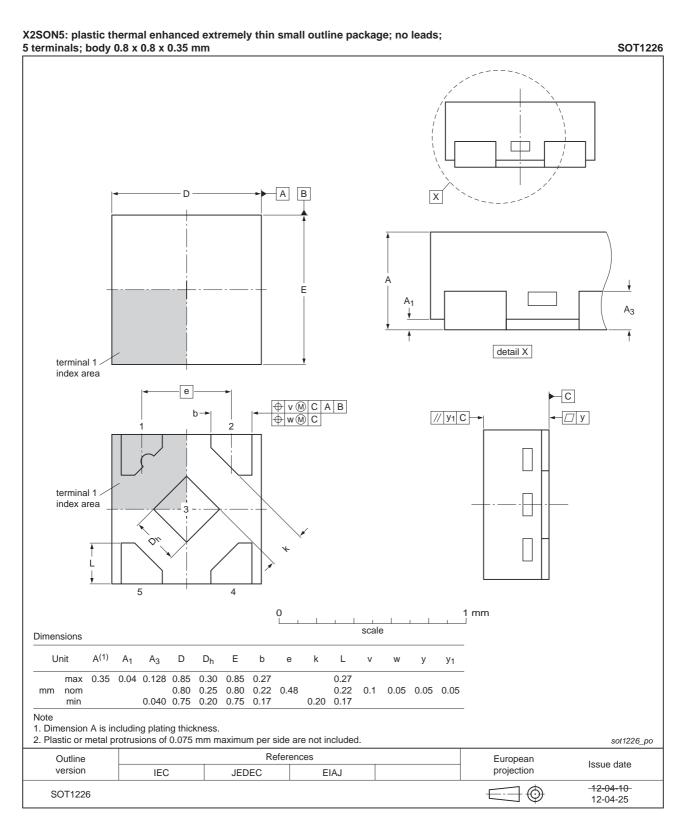


Fig 21. Package outline SOT1226 (X2SON5)

### Low-power Schmitt trigger inverter

# 18. Abbreviations

#### Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

# 19. Revision history

#### Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G14 v.6	20120628	Product data sheet	-	74AUP1G14 v.5
Modifications:	<ul> <li>Added type null</li> </ul>	mber 74AUP1G14GX (SOT1226)		
	<ul> <li>Package outlin</li> </ul>	e drawing of SOT886 (Figure 17)	modified.	
74AUP1G14 v.5	20111128	Product data sheet	-	74AUP1G14 v.4
Modifications:	<ul> <li>Legal pages up</li> </ul>	odated.		
74AUP1G14 v.4	20100713	Product data sheet	-	74AUP1G14 v.3
74AUP1G14 v.3	20090708	Product data sheet	-	74AUP1G14 v.2
74AUP1G14 v.2	20060828	Product data sheet	-	74AUP1G14 v.1
74AUP1G14 v.1	20050718	Product data sheet	-	-

#### Low-power Schmitt trigger inverter

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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#### Low-power Schmitt trigger inverter

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#### Low-power Schmitt trigger inverter

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